

IPC302N20N3X1SA1

IPC302N20N3X1SA1 Information

Heisener.com

Part Number IPC302N20N3X1SA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V BARE DIE

Package Die

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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IPC302N20N3X1SA1 Specifications

Manufacturer Part NumberIPC302N20N3X1SA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 260µAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package Die Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Surface Mount Surface Mount Package / Case Die	Manufacturer Part Number	IPC302N20N3X1SA1
PackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 260μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs100 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Manufacturer	Infineon Technologies
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Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 10V Operating Temperature - Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Vgs (Max)	-
Rds On (Max) @ Id, Vgs 100 mOhm @ 2A, 10V Operating Temperature	FET Feature	-
Operating Temperature Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Power Dissipation (Max)	-
Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Rds On (Max) @ Id, Vgs	100 mOhm @ 2A, 10V
Supplier Device Package Sawn on foil Package / Case Die	Operating Temperature	-
Package / Case Die	Mounting Type	Surface Mount
-	Supplier Device Package	Sawn on foil
Report errors?	Package / Case	Die
		Report errors?

IPC302N20N3X1SA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPC302N20N3X1SA1 Payment Methods



















IPC302N20N3X1SA1 Shipping Methods













If you have any question about IPC302N20N3X1SA1, please do not hesitate to contact us!

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